AMENDMENT & RESPONSE UNDER 37 C.F.R. § 1.116 - EXPEDITED PROCEDURE

Serial Number: 09/470,265

Filing Date: December 22, 1999

DEVICES HAVING IMPROVED CAPACITANCE AND METHODS OF THEIR FABRICATION

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a second conductive capacitor plate; and

[a dielectric interposed between said first and second conductive capacitor plates, wherein said dielectric is an oxide of a metal layer of a second material overlying the first conductive capacitor plate, wherein the metal layer includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion is a dielectric of the capacitor; and

a processor configured to access the monolithic memory device.

- 53. (Amended) A capacitor comprising:
  - a first capacitor electrode;

[a dielectric layer that includes an oxide of] a metal layer overlying the first capacitor electrode, wherein the metal layer includes a non-oxidized portion and an oxidized portion, wherein the oxidized portion is a dielectric of the capacitor; and

a second capacitor electrode.

- 79. (Amended) The capacitor of claim 19, wherein the [oxide] oxidized portion of the metal layer is formed from at least one metal selected from the group consisting of titanium, copper, gold, tungsten, and nickel.
- 82. (Amended) The memory system of claim 20, wherein the [oxide] oxidized portion of the metal layer is formed from at least one metal selected from the group consisting of titanium, copper, gold, tungsten, and nickel.
- 85. The capacitor of claim 53, wherein the [dielectric layer] oxidized portion (Amended) of the metal layer is formed from at least one metal selected from the group consisting of titanium, copper, gold, tungsten, and nickel.
- The capacitor of claim 19, wherein the [oxide] oxidized portion of the (Amended) metal layer comprises titanium.

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108. (Amended) The capacitor of claim 19, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive plate and the [oxide] oxidized portion of the metal layer.

- 109. (Amended) The memory system of claim 20, wherein the [oxide] <u>oxidized portion</u> of the metal layer comprises titanium.
- 110. (Amended) The memory system of claim 20, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first conductive plate and the [oxide] oxidized portion of the metal layer.
- 111. (Amended) The capacitor of claim 53, wherein the [dielectric layer] <u>oxidized portion</u> of the metal layer comprises titanium.
- 112. (Amended) The capacitor of claim 53, further comprising at least one of a diffusion barrier layer and an oxidation resistant layer interposed between the first capacitor electrode and the [dielectric layer] oxidized portion of the metal layer.